

APT802R4CN	800V	4.5A	2.40Ω
APT752R4CN	750V	4.5A	2.40Ω
APT802R8CN	800V	4.0A	2.80Ω
APT752R8CN	750V	4.0A	2.80Ω

POWER MOS IV™

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT 752R4CN	APT 802R4CN	APT 752R8GCN	APT 802R8CN	UNIT
V _{DSS}	Drain-Source Voltage	750	800	750	800	Volts
I _D	Continuous Drain Current @ T _C = 25°C	4.5		4.0		Amps
I _{DM}	Pulsed Drain Current ①	18		16		
V _{GS}	Gate-Source Voltage	±30				Volts
P _D	Total Power Dissipation @ T _C = 25°C	125				Watts
	Linear Derating Factor	1.0				W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150				°C
T _L	Lead Temperature: 0.063" from Case for 10 Sec.	300				

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	APT802R4CN / APT802R8CN	800		Volts
		APT752R4CN / APT752R8CN	750		
$I_{D(ON)}$	On State Drain Current ② ($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT802R4CN / APT752R4CN	4.5		Amps
		APT802R8CN / APT752R8CN	4.0		
$R_{DS(ON)}$	Drain-Source On-State Resistance ② ($V_{GS} = 10V, 0.5 I_D$ [Cont.])	APT802R4CN / APT752R4CN		2.40	Ohms
		APT802R8CN / APT752R8CN		2.80	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1.0mA$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			1.00	°C/W
$R_{\theta JA}$	Junction to Ambient			50	

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DYNAMIC CHARACTERISTICS

APT802R4/752R4/802R8/752R8CN

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{DC}	Drain-to-Case Capacitance	$f = 1 \text{ MHz}$		15	22	pF
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		790	950	
C_{oss}	Output Capacitance			116	163	
C_{rss}	Reverse Transfer Capacitance			44	66	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		38	55	nC
Q_{gs}	Gate-Source Charge			4.5	7	
Q_{gd}	Gate-Drain ("Miller") Charge			16	24	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		10	20	ns
t_r	Rise Time			11	22	
$t_d(\text{off})$	Turn-off Delay Time			35	53	
t_f	Fall Time			13	26	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT802R4CN / APT752R4CN		4.5	Amps
		APT802R8CN / APT752R8CN		4.0	
I_{SM}	Pulsed Source Current ① (Body Diode)	APT802R4CN / APT752R4CN		18	
		APT802R8CN / APT752R8CN		16	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100\text{A}/\mu\text{s}$)	160	320	640	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100\text{A}/\mu\text{s}$)	1.5	3.0	6.0	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1 \text{ Sec.}$	125			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}], V_{DS} = P_D / I_D [\text{Cont.}], t = 1 \text{ Sec.}$	125			
I_{LM}	Inductive Current Clamped	APT802R4CN / APT752R4CN	18			Amps
		APT802R8CN / APT752R8CN	16			

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig. 1)

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

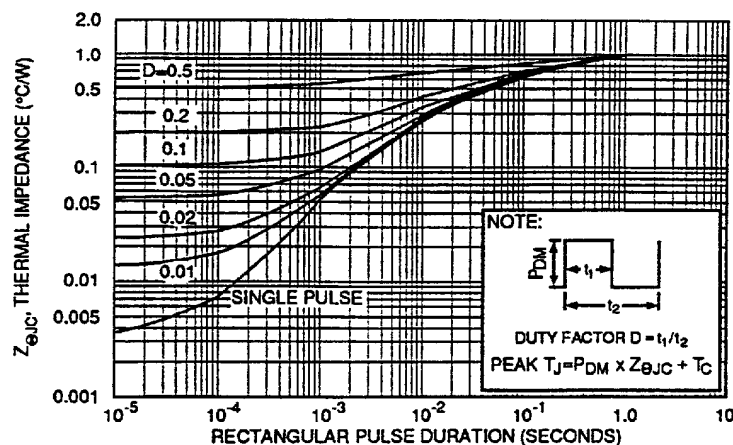


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT802R4/752R4/802R8/752R8CN

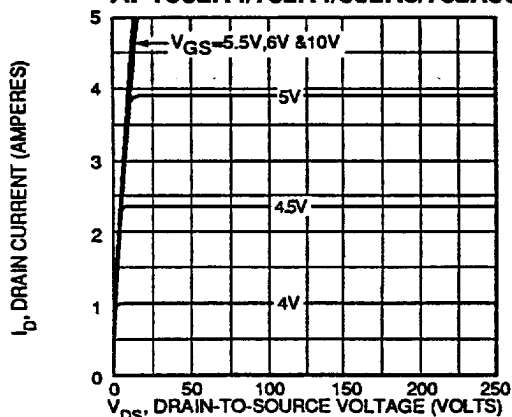


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

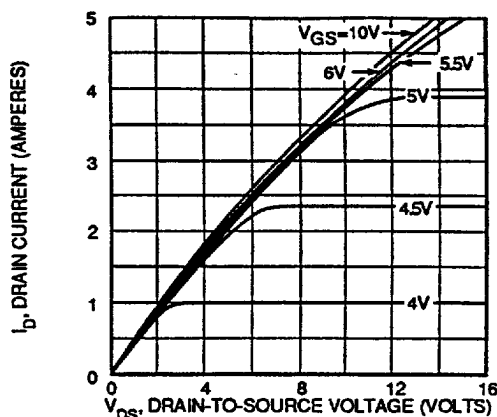


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

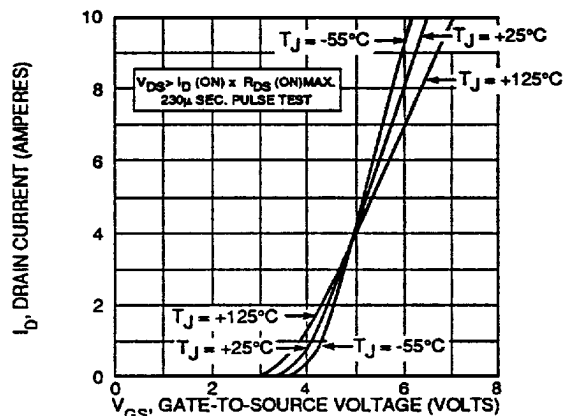


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

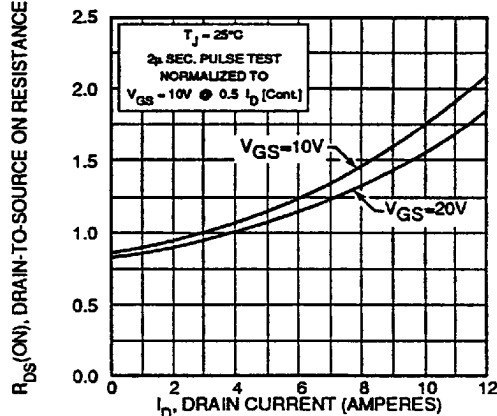


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

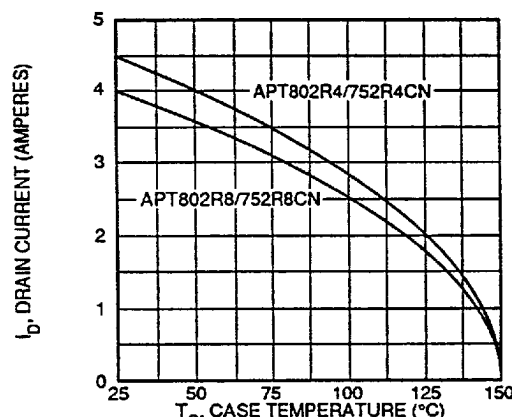


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

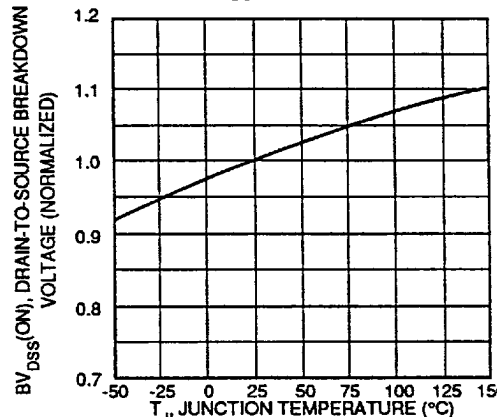


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

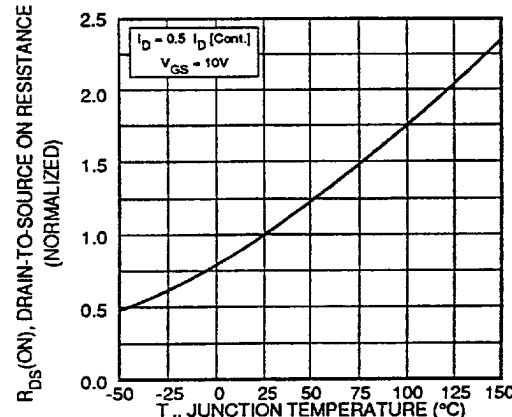


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

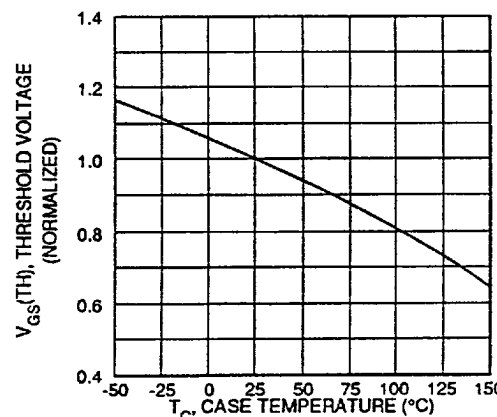


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

APT802R4/752R4/802R8/752R8CN

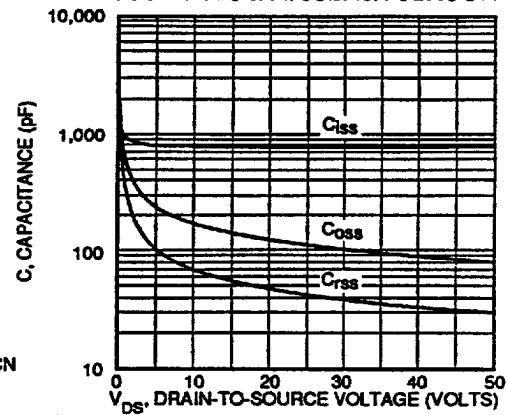
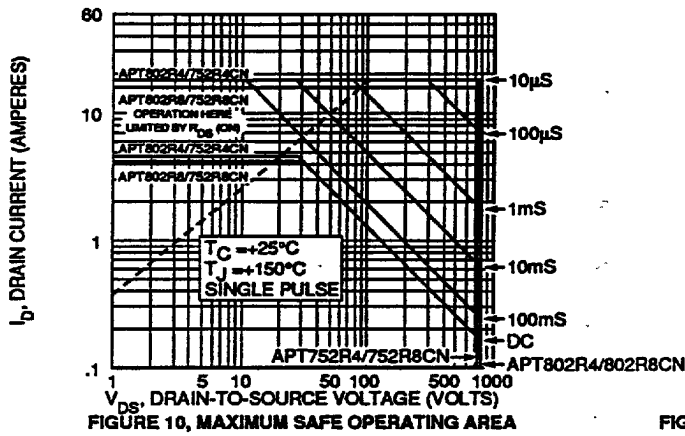


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

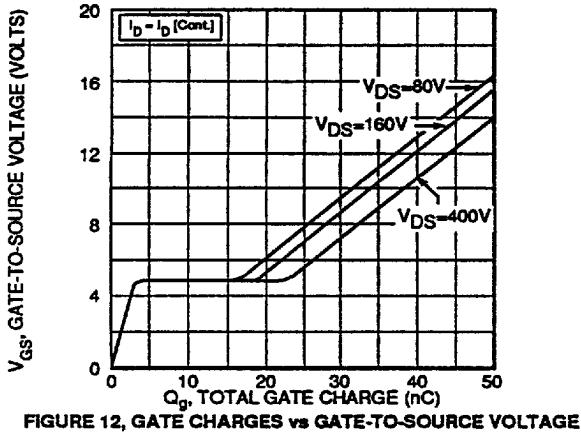


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

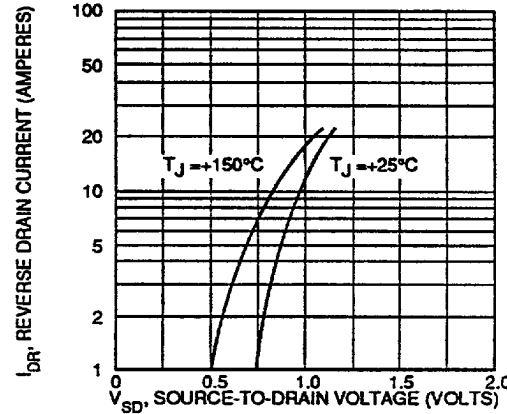
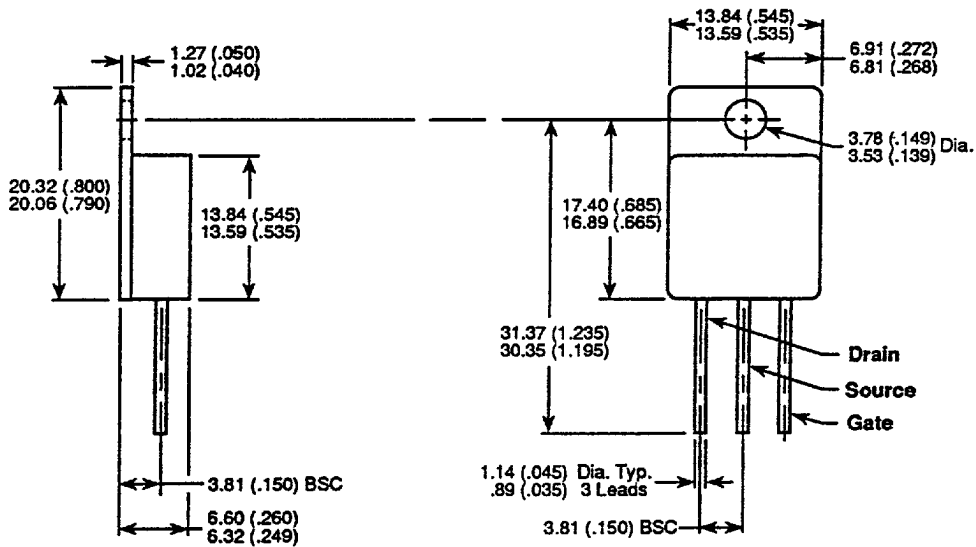


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-254AA Package Outline



Dimensions in Millimeters and (Inches)